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				Application Number	Not yet assigned
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				Filing Date	July 19, 2006
				First Named Inventor	Tsuguo FUKUDA et al.
				Art Unit	
Examiner Name					
Attorney Docket Number	062697				
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
/MC/	1	US 6,273,948	B1	8/14/2001	Porowski et al.
/MC/	2	US 6,270,569	B1	8/7/2001	Shibata et al.
/MC/	3	US 6,592,663	B1	7/15/2003	Sarayama et al.
/MC/	4	US 5,363,799		11/15/1994	Yonehara et al.
/MC/	5	US 2004/0144300	A1	7/29/2004	Kitaoka et al.

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
/MC/	6	JP	56-160400	A	12/10/1981	Matsushita Electrical Industrial Co., Ltd.	Abstract; Cited in ISR
/MC/	7	JP	1-132117	A	5/24/1989	Canon Inc.	Abstract; Cited in ISR; Corresponds to #4
/MC/	8	JP	2004-244307	A	9/2/2004	Matsushita Electric Industrial Co., Ltd.	Abstract; Cited in ISR; Corresponds to #5
/MC/	9	JP	2001-131741	A	5/15/2001	Sony Corp	Abstract; Cited in ISR

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
/MC/	10	M.K. KELLY et al., "Optical patterning of GaN films", Appl. Phys. Lett. 69 (12), 16 September 1996	
/MC/	11	W.S. WONG et al., "Fabrication of thin-film InGaN light-emitting diode membranes by laser lift-off", Applied Physics Letters, Volume 75, Number 10, 6 September 1999	
/MC/	12	TAKAYUKI INOUE et al., "Growth of Bulk GaN Single Crystals by the Pressure-Controlled...", Central R&D Laboratory, Japan Energy Corporation, Faculty of Engineering, Yamaguchi University, May 15, 2000	
/MC/	13	S. POROWSKI et al., "Thermodynamical properties of III-V nitrides and crystal growth of...", Journal of Crystal Growth 178 (1997) 174-188	
/MC/	14	International Search Report mailed April 5, 2005 of International Application PCT/JP2005/000696	

Examiner Signature	/Marissa Chaet/	Date Considered	08/09/2007
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